

FQP19N20C/FQPF19N20C

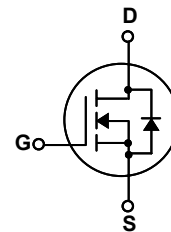
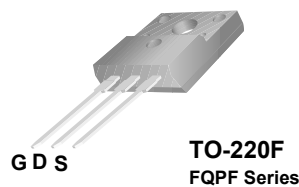
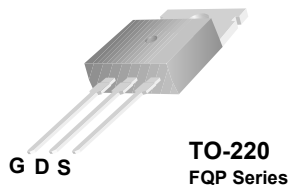
200V N-Channel MOSFET

General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switching DC/DC converters, switch mode power supplies, DC-AC converters for uninterrupted power supplies and motor controls.

Features

- 19.0A, 200V, $R_{DS(on)} = 0.17\Omega @ V_{GS} = 10V$
- Low gate charge (typical 40.5 nC)
- Low Crss (typical 85 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FQP19N20C	FQPF19N20C	Units
V_{DSS}	Drain-Source Voltage	200		V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$) - Continuous ($T_C = 100^\circ\text{C}$)	19.0	19.0 *	A
		12.1	12.1 *	A
I_{DM}	Drain Current - Pulsed (Note 1)	76.0	76.0 *	A
V_{GSS}	Gate-Source Voltage	± 30		V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	433		mJ
I_{AR}	Avalanche Current (Note 1)	19.0		A
E_{AR}	Repetitive Avalanche Energy (Note 1)	13.9		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	5.5		V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$) - Derate above 25°C	139	43	W
		1.11	0.34	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150		$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300		$^\circ\text{C}$

* Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	FQP19N20C	FQPF19N20C	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.9	2.89	$^\circ\text{C}/\text{W}$
$R_{\theta JS}$	Thermal Resistance, Case-to-Sink Typ.	0.5	--	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	62.5	$^\circ\text{C}/\text{W}$

Electrical Characteristics

$T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	200	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C	--	0.24	--	$\text{V}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}$	--	--	10	μA
		$V_{DS} = 160\text{ V}, T_C = 125^\circ\text{C}$	--	--	100	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 9.5\text{ A}$	--	0.14	0.17	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 40\text{ V}, I_D = 9.5\text{ A}$ (Note 4)	--	10.8	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	830	1080	pF
C_{oss}	Output Capacitance		--	195	255	pF
C_{riss}	Reverse Transfer Capacitance		--	85	110	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 100\text{ V}, I_D = 19.0\text{ A},$ $R_G = 25\ \Omega$	--	15	40	ns
t_r	Turn-On Rise Time		--	150	310	ns
$t_{d(off)}$	Turn-Off Delay Time		--	135	280	ns
t_f	Turn-Off Fall Time		(Note 4, 5)	--	115	240
Q_g	Total Gate Charge	$V_{DS} = 160\text{ V}, I_D = 19.0\text{ A},$ $V_{GS} = 10\text{ V}$	--	40.5	53.0	nC
Q_{gs}	Gate-Source Charge		--	6.0	--	nC
Q_{gd}	Gate-Drain Charge		(Note 4, 5)	--	22.5	--

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current	--	--	19.0	A	
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	76.0	A	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 19.0\text{ A}$	--	--	1.5	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 19.0\text{ A},$	--	208	--	ns
Q_{rr}	Reverse Recovery Charge	$di_F / dt = 100\text{ A}/\mu\text{s}$ (Note 4)	--	1.63	--	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 1.8\text{ mH}, I_{AS} = 19.0\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 19.0\text{ A}, di/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\ \mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

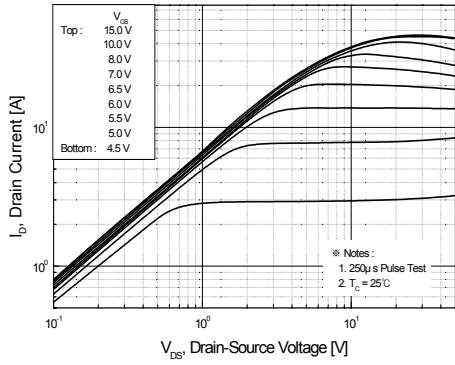


Figure 1. On-Region Characteristics

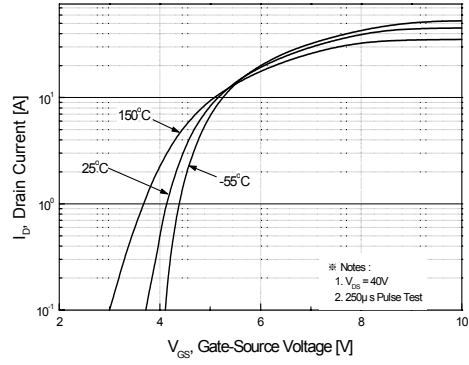


Figure 2. Transfer Characteristics

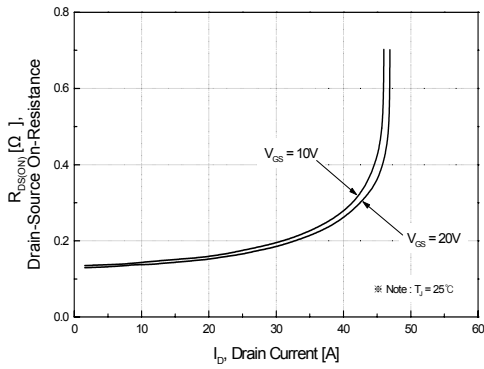


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

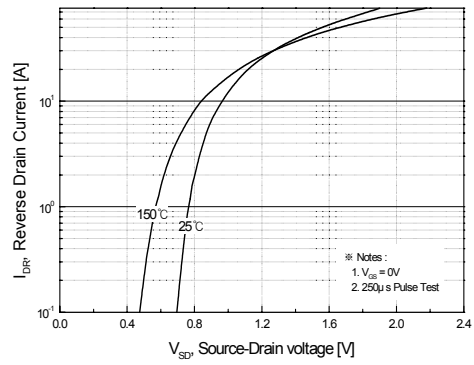


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

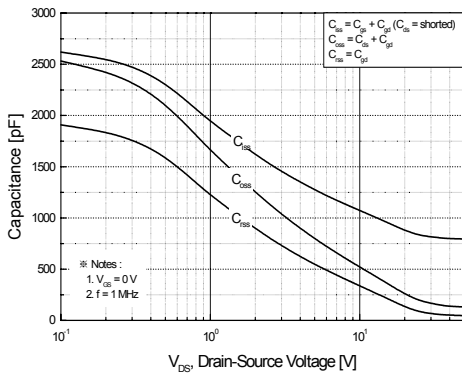


Figure 5. Capacitance Characteristics

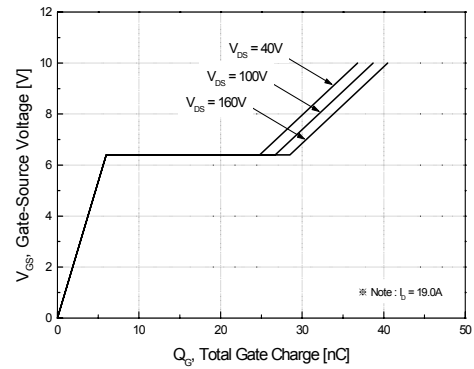


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

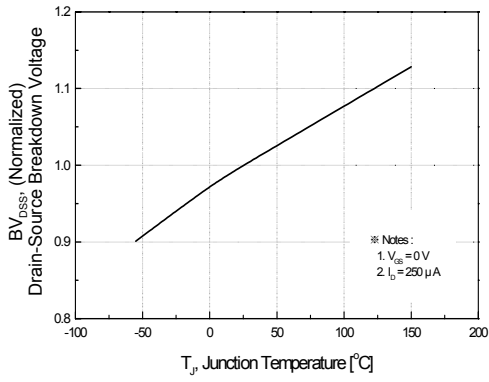


Figure 7. Breakdown Voltage Variation vs Temperature

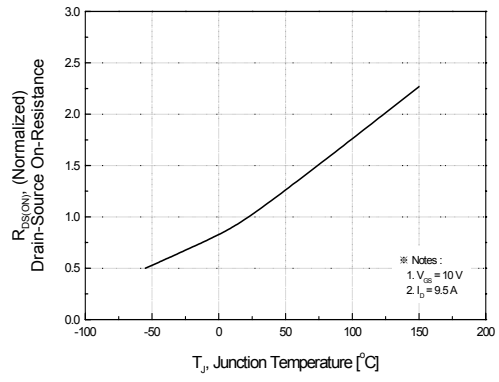


Figure 8. On-Resistance Variation vs Temperature

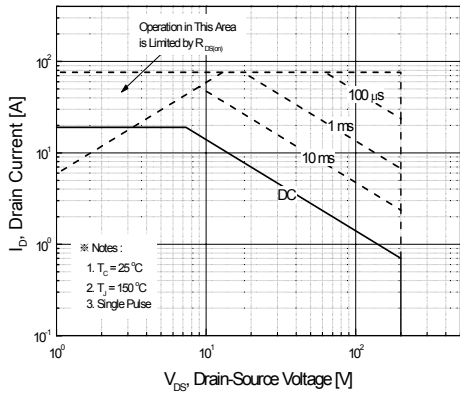


Figure 9-1. Maximum Safe Operating Area for FQP19N20C

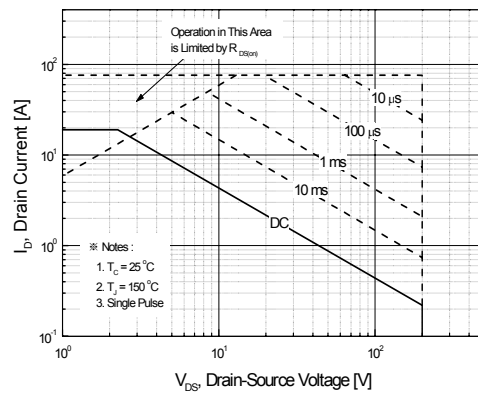


Figure 9-2. Maximum Safe Operating Area for FQPF19N20C

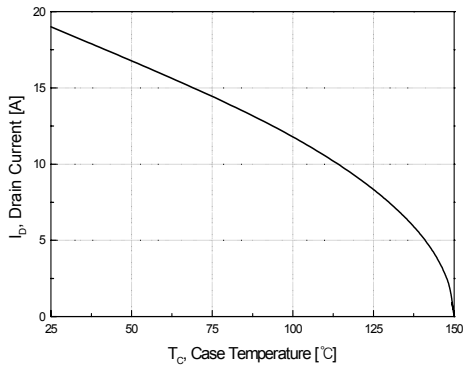


Figure 10. Maximum Drain Current vs Case Temperature

Typical Characteristics (Continued)

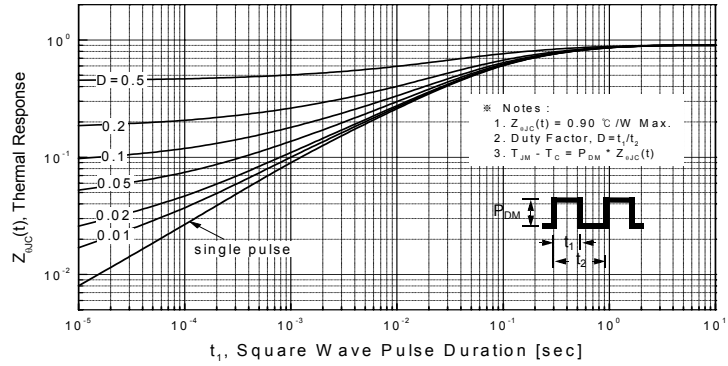


Figure 11-1. Transient Thermal Response Curve for FQP19N20C

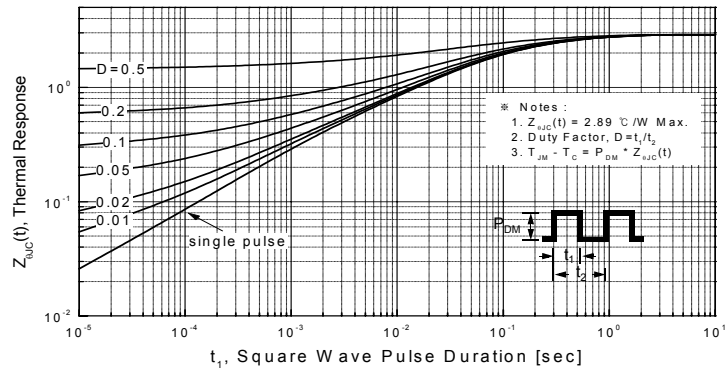
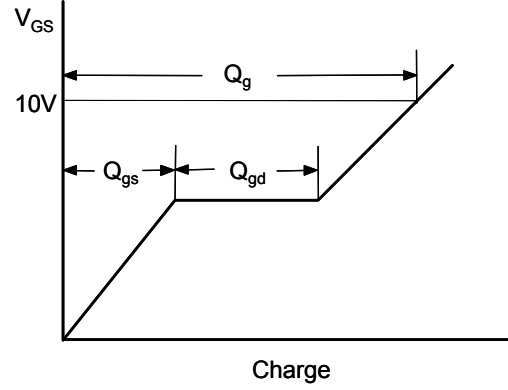
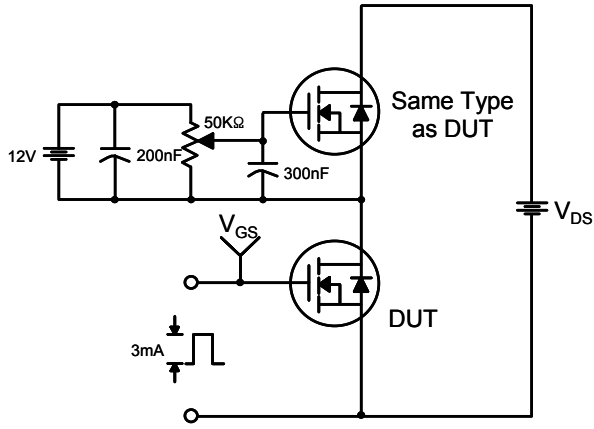
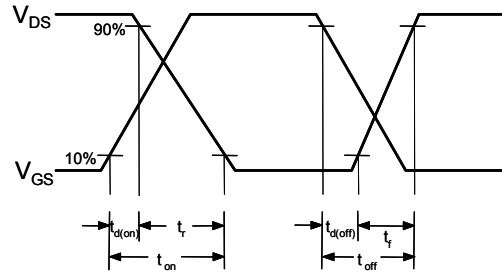
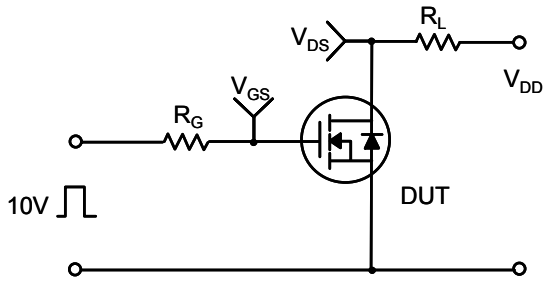


Figure 11-2. Transient Thermal Response Curve for FQPF19N20C

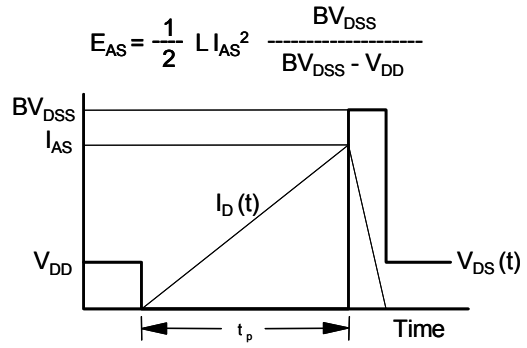
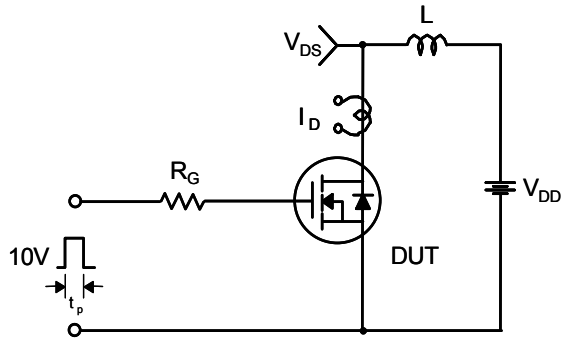
Gate Charge Test Circuit & Waveform



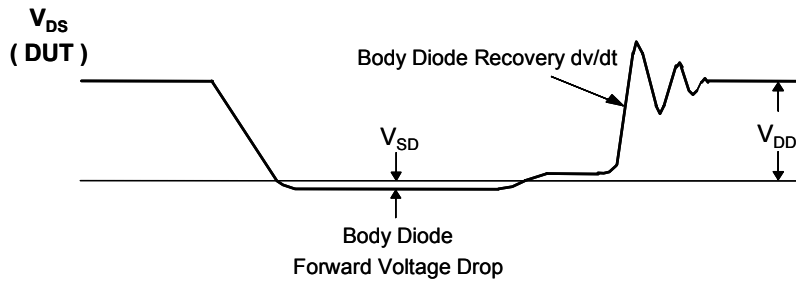
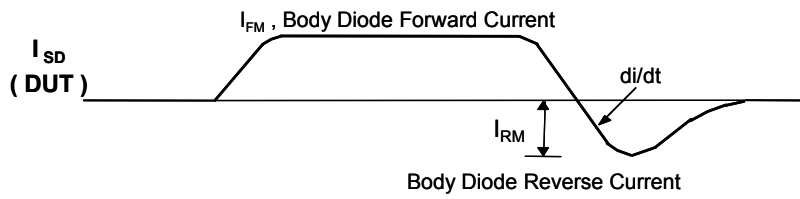
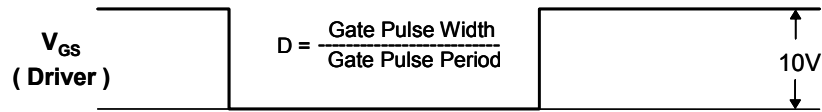
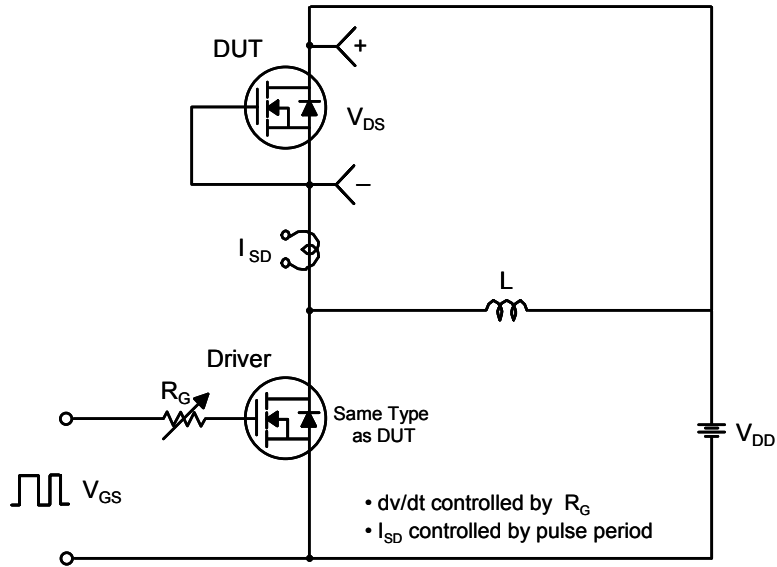
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

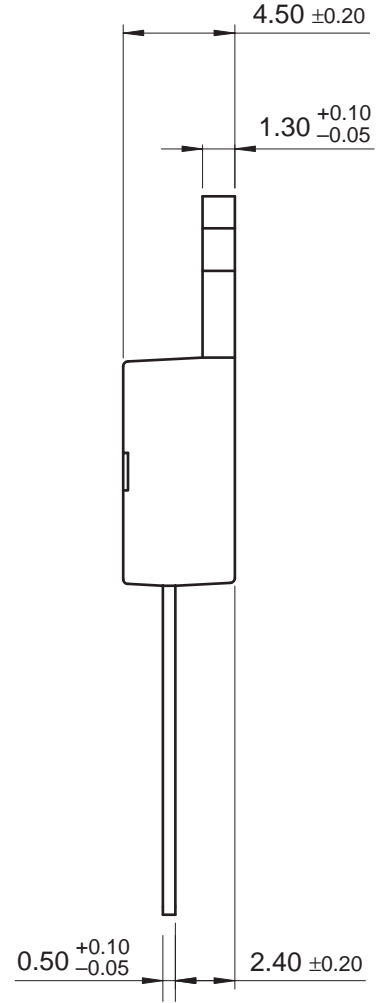
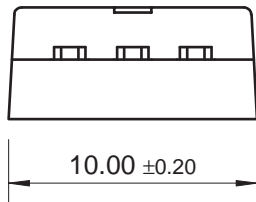
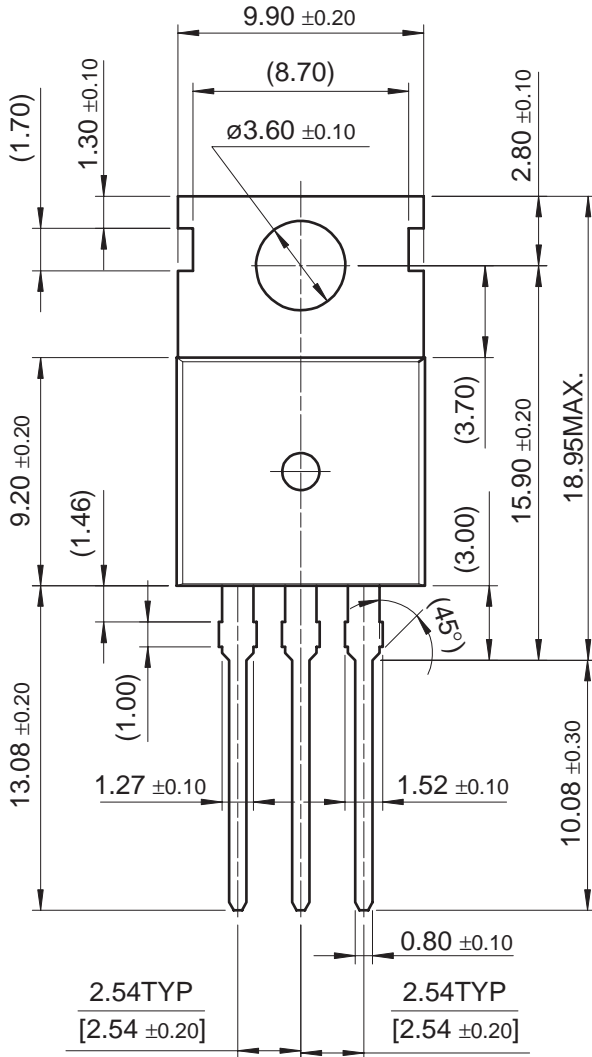


Peak Diode Recovery dv/dt Test Circuit & Waveforms



Package Dimensions

TO-220

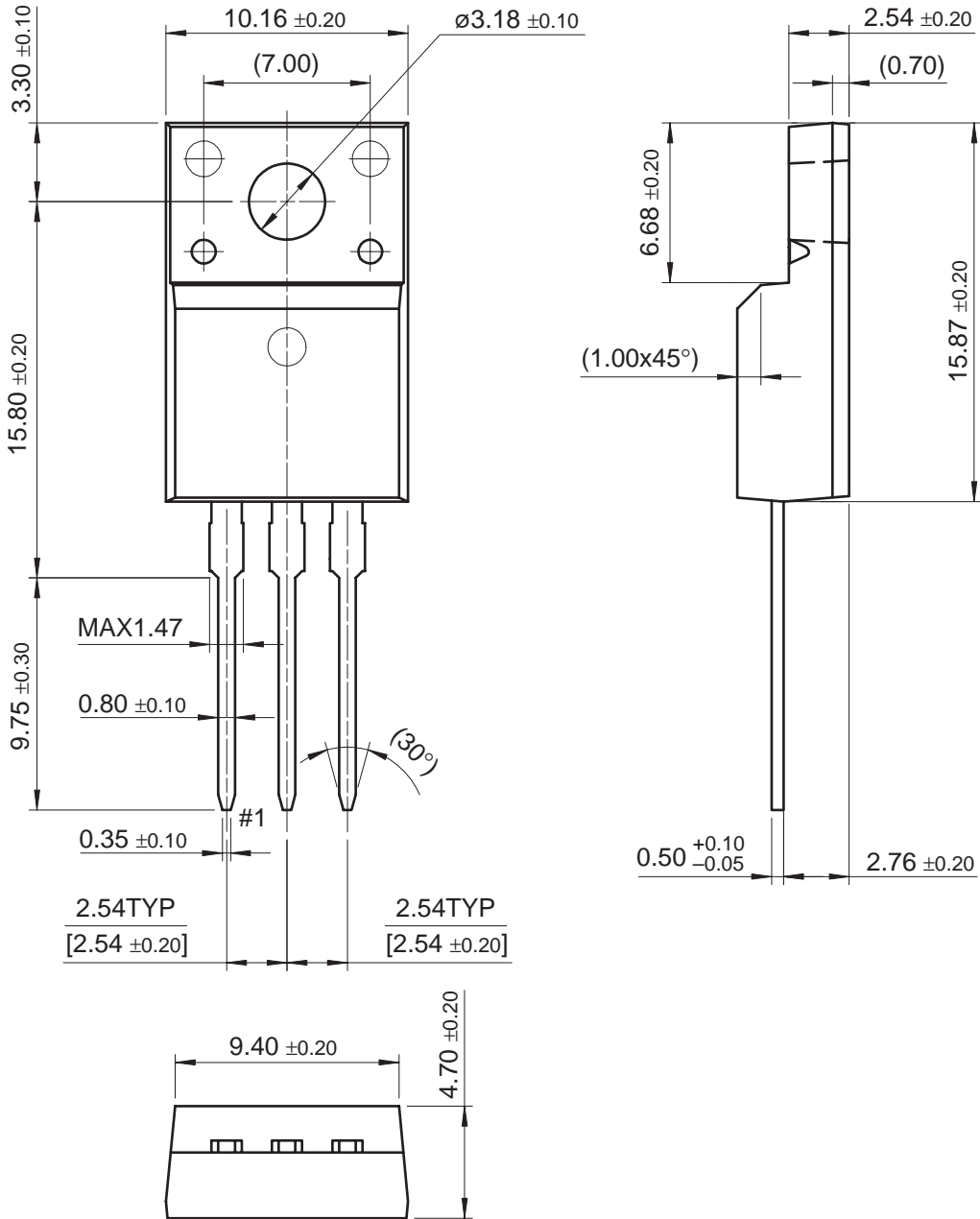


FQP19N20C/FQPF19N20C

Dimensions in Millimeters

Package Dimensions (Continued)

TO-220F



FQP19N20C/FQPF19N20C

Dimensions in Millimeters

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